## MC74HC245A

## Octal 3-State Noninverting Bus Transceiver

## High-Performance Silicon-Gate CMOS

The MC74HC245A is identical in pinout to the LS245. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

The HC245A is a 3-state noninverting transceiver that is used for 2 -way asynchronous communication between data buses. The device has an active-low Output Enable pin, which is used to place the I/O ports into high-impedance states. The Direction control determines whether data flows from A to B or from B to A .

## Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: $1 \mu \mathrm{~A}$
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 308 FETs or 77 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free and are RoHS Compliant


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MARKING DIAGRAMS

|  | 20 |
| :---: | :---: |
| 20 |  |
| H月H日B | HC |
| HC245A | 245A |
| AWLYYWWG | ALYW- |
| $\bigcirc$ | $\bigcirc$ |
|  |  |
| 1 | 1 |
| SOIC-20 | TSSOP-20 |

$$
\begin{array}{ll}
\text { A } & =\text { Assembly Location } \\
\text { WL, L } & =\text { Wafer Lot } \\
\text { YY, Y } & =\text { Year } \\
\text { WW, W } & =\text { Work Week } \\
\text { G or } & =\text { Pb-Free Package }
\end{array}
$$

(Note: Microdot may be in either location)

ORDERING INFORMATION
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

## FUNCTION TABLE

| Control Inputs |  |  |
| :---: | :---: | :--- |
| Output <br> Enable | Direction |  |
| L | L | Data Transmitted from Bus B to Bus A |
| L | H | Data Transmitted from Bus A to Bus B |
| H | X | Buses Isolated (High-Impedance State) |

X = don't care

MAXIMUM RATINGS (Note 1)

| Symbol | Parameter | Value | Unit |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage | -0.5 to +7.0 | V |
| $\mathrm{V}_{\text {IN }}$ | DC Input Voltage | -0.5 to $\mathrm{V}_{\mathrm{CC}}+0.5$ | V |
| V OUT | DC Output Voltage (Note 2) | -0.5 to $\mathrm{V}_{\mathrm{CC}}+0.5$ | $\checkmark$ |
| IIK | DC Input Diode Current | $\pm 20$ | mA |
| lok | DC Output Diode Current | $\pm 35$ | mA |
| Iout | DC Output Sink Current | $\pm 35$ | mA |
| Icc | DC Supply Current per Supply Pin | $\pm 75$ | mA |
| $\mathrm{I}_{\text {GND }}$ | DC Ground Current per Ground Pin | $\pm 75$ | mA |
| $\mathrm{T}_{\text {STG }}$ | Storage Temperature Range | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{L}}$ | Lead Temperature, 1 mm from Case for 10 Seconds | 260 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{J}$ | Junction Temperature Under Bias | +150 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\text {JA }}$ | Thermal Resistance $\begin{aligned} & \text { SOIC } \\ & \text { TSSOP }\end{aligned}$ | $\begin{gathered} 96 \\ 128 \end{gathered}$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{P}_{\mathrm{D}}$ | Power Dissipation in Still Air at $85^{\circ} \mathrm{C}$ SSOIC TSSOP | $\begin{aligned} & 500 \\ & 450 \end{aligned}$ | mW |
| MSL | Moisture Sensitivity | Level 1 |  |
| $\mathrm{F}_{\mathrm{R}}$ | Flammability Rating Oxygen Index: 30\% to 35\% | UL 94 V-0 @ 0.125 in |  |
| $\mathrm{V}_{\text {ESD }}$ | ESD Withstand VoltageHuman Body Model (Note 3) <br> Machine Model (Note 4) <br> Charged Device Model (Note 5) | $\begin{aligned} & >2000 \\ & >200 \\ & >1000 \end{aligned}$ | V |
| LLATCHUP | Latchup Performance $\quad$ Above $\mathrm{V}_{\mathrm{CC}}$ and Below GND at $85^{\circ} \mathrm{C}$ (Note 6) | $\pm 300$ | mA |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm -by- 1 inch, 20 ounce copper trace with no air flow.
2. Io absolute maximum rating must observed.
3. Tested to EIA/JESD22-A114-A.
4. Tested to EIA/JESD22-A115-A.
5. Tested to JESD22-C101-A.
6. Tested to EIA/JESD78.

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter |  | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{C C}$ | DC Supply Voltage (Referenced to GND) |  | 2.0 | 6.0 | V |
| $V_{\text {in }}, V_{\text {out }}$ | DC Input Voltage, Output Voltage (Referenced to GND) |  | 0 | $\mathrm{V}_{\mathrm{cc}}$ | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature, All Package Types |  | -55 | +125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{tr}_{\mathrm{r}}, \mathrm{t}_{\mathrm{f}}$ | Input Rise and Fall Time (Figure 1) | $\begin{aligned} & \mathrm{V}_{\mathrm{CC}}=2.0 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CC}}=4.5 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CC}}=6.0 \mathrm{~V} \end{aligned}$ | 0 0 0 | $\begin{gathered} 1000 \\ 500 \\ 400 \end{gathered}$ | ns |

[^0] the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| Symbol | Parameter | Test Conditions | $\underset{\mathrm{Vc}}{\mathrm{v}_{\mathrm{cc}}}$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $\begin{gathered} -55 \text { to } \\ 25^{\circ} \mathrm{C} \end{gathered}$ | $\leq 85^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Minimum High-Level Input Voltage | $\begin{aligned} & \mathrm{V}_{\text {out }}=\mathrm{V}_{\mathrm{CC}}-0.1 \mathrm{~V} \\ & \\|_{\text {out }} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \hline 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{gathered} \hline 1.5 \\ 2.1 \\ 3.15 \\ 4.2 \end{gathered}$ | $\begin{gathered} \hline 1.5 \\ 2.1 \\ 3.15 \\ 4.2 \end{gathered}$ | $\begin{gathered} \hline 1.5 \\ 2.1 \\ 3.15 \\ 4.2 \end{gathered}$ | V |
| $\mathrm{V}_{\text {IL }}$ | Maximum Low-Level Input Voltage | $\begin{aligned} & \mathrm{V}_{\text {out }}=0.1 \mathrm{~V} \\ & \left.\right\|_{\text {out }} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \hline 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \\ & \hline \end{aligned}$ | $\begin{gathered} \hline 0.5 \\ 0.9 \\ 1.35 \\ 1.8 \\ \hline \end{gathered}$ | $\begin{gathered} \hline 0.5 \\ 0.9 \\ 1.35 \\ 1.8 \\ \hline \end{gathered}$ | $\begin{gathered} \hline 0.5 \\ 0.9 \\ 1.35 \\ 1.8 \\ \hline \end{gathered}$ | V |
| $\mathrm{V}_{\mathrm{OH}}$ | Minimum High-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\text {IH }} \\ & \left.\right\|_{l_{\text {out }}} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \hline 2.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 4.4 \\ & 5.9 \end{aligned}$ | $\begin{aligned} & 1.9 \\ & 4.4 \\ & 5.9 \end{aligned}$ | $\begin{aligned} & \hline 1.9 \\ & 4.4 \\ & 5.9 \end{aligned}$ | V |
|  |  |  | $\begin{aligned} & \hline 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 2.48 \\ & 3.98 \\ & 5.48 \end{aligned}$ | $\begin{aligned} & \hline 2.34 \\ & 3.84 \\ & 5.34 \end{aligned}$ | $\begin{aligned} & 2.2 \\ & 3.7 \\ & 5.2 \end{aligned}$ |  |
| VoL | Maximum Low-Level Output Voltage | $\begin{aligned} & \mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{IL}} \\ & \left.\right\|_{\text {lout }} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{aligned} & \hline 2.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ | $\begin{aligned} & 0.1 \\ & 0.1 \\ & 0.1 \end{aligned}$ | V |
|  |  | $\mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{IL}} \left\lvert\, \begin{array}{ll} \mid l_{\text {out }} & \leq 2.4 \mathrm{~mA} \\ & \\|_{\text {out }} \\ \left\|\left.\right\|_{\text {out }}\right\| & \leq 7.0 \mathrm{~mA} \\ \leq 7.8 \mathrm{~mA} \end{array}\right.$ | $\begin{aligned} & \hline 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & \hline 0.26 \\ & 0.26 \\ & 0.26 \end{aligned}$ | $\begin{aligned} & \hline 0.33 \\ & 0.33 \\ & 0.33 \end{aligned}$ | $\begin{aligned} & \hline 0.4 \\ & 0.4 \\ & 0.4 \end{aligned}$ |  |
| 1 in | Maximum Input Leakage Current | $\mathrm{V}_{\text {in }}=\mathrm{V}_{\text {cc }}$ or GND | 6.0 | $\pm 0.1$ | $\pm 1.0$ | $\pm 1.0$ | $\mu \mathrm{A}$ |
| loz | Maximum Three-State Leakage Current | Output in High-Impedance State $\mathrm{V}_{\text {in }}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}}$ <br> $V_{\text {out }}=V_{\text {CC }}$ or GND | 6.0 | $\pm 0.5$ | $\pm 5.0$ | $\pm 10$ | $\mu \mathrm{A}$ |
| Icc | Maximum Quiescent Supply Current (per Package) | $\begin{aligned} & V_{\text {in }}=V_{C C} \text { or GND } \\ & I_{\text {out }}=0 \mu \mathrm{~A} \end{aligned}$ | 6.0 | 4.0 | 40 | 160 | $\mu \mathrm{A}$ |

AC ELECTRICAL CHARACTERISTICS $\left(C_{L}=50 \mathrm{pF}\right.$, Input $\left.\mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=6 \mathrm{~ns}\right)$

|  | Parameter | $\begin{gathered} \mathrm{v}_{\mathrm{cc}} \\ \mathrm{~V} \end{gathered}$ | Guaranteed Limit |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Symbol |  |  | $\begin{gathered} -55 \text { to } \\ 25^{\circ} \mathrm{C} \end{gathered}$ | $\leq 85^{\circ} \mathrm{C}$ | $\leq 125^{\circ} \mathrm{C}$ |  |
| $\begin{aligned} & \hline \mathrm{t}_{\mathrm{PLLH}}, \\ & \mathrm{t}_{\text {PHL }} \end{aligned}$ | Maximum Propagation Delay, A to B, B to A <br> (Figures 1 and 3 ) | $\begin{aligned} & 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \\ & \hline \end{aligned}$ | $\begin{aligned} & 75 \\ & 55 \\ & 15 \\ & 13 \\ & \hline \end{aligned}$ | $\begin{aligned} & \hline 95 \\ & 70 \\ & 19 \\ & 16 \\ & \hline \end{aligned}$ | $\begin{gathered} \hline 110 \\ 80 \\ 22 \\ 19 \\ \hline \end{gathered}$ | ns |
| $\begin{aligned} & \hline \mathrm{t}_{\text {PLZ }}, \\ & \mathrm{t}_{\mathrm{PHZ}} \end{aligned}$ | Maximum Propagation Delay, Direction or Output Enable to A or B (Figures 2 and 4) | $\begin{aligned} & \hline 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \\ & \hline \end{aligned}$ | $\begin{gathered} \hline 110 \\ 90 \\ 22 \\ 19 \\ \hline \end{gathered}$ | $\begin{gathered} \hline 140 \\ 110 \\ 28 \\ 24 \\ \hline \end{gathered}$ | $\begin{gathered} 165 \\ 130 \\ 33 \\ 28 \\ \hline \end{gathered}$ | ns |
| $\begin{aligned} & \hline \mathrm{t}_{\mathrm{PZL}}, \\ & \mathrm{t}_{\mathrm{PZH}} \end{aligned}$ | Maximum Propagation Delay, Output Enable to A or B (Figures 2 and 4) | $\begin{aligned} & \hline 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \\ & \hline \end{aligned}$ | $\begin{gathered} \hline 110 \\ 90 \\ 22 \\ 19 \\ \hline \end{gathered}$ | $\begin{gathered} \hline 140 \\ 110 \\ 28 \\ 24 \\ \hline \end{gathered}$ | $\begin{gathered} \hline 165 \\ 130 \\ 33 \\ 28 \\ \hline \end{gathered}$ | ns |
| $\begin{aligned} & \mathrm{t}_{\mathrm{TLH}}, \\ & \mathrm{t}_{\mathrm{TH}}, \end{aligned}$ | Maximum Output Transition Time, Any Output <br> (Figures 1 and 3 ) | $\begin{aligned} & \hline 2.0 \\ & 3.0 \\ & 4.5 \\ & 6.0 \end{aligned}$ | $\begin{aligned} & 60 \\ & 23 \\ & 12 \\ & 10 \end{aligned}$ | $\begin{aligned} & 75 \\ & 27 \\ & 15 \\ & 13 \end{aligned}$ | $\begin{aligned} & 90 \\ & 32 \\ & 18 \\ & 15 \end{aligned}$ | ns |
| $\mathrm{C}_{\text {in }}$ | Maximum Input Capacitance (Pin 1 or Pin 19) | - | 10 | 10 | 10 | pF |
| $\mathrm{C}_{\text {out }}$ | Maximum Three-State I/O Capacitance (I/O in High-Impedance State) | - | 15 | 15 | 15 | pF |
|  | Power Dissipation Capacitance (Per Transceiver Channel) (Note 7) |  | Typical @ $25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{cc}}=5.0 \mathrm{~V}$ |  |  | pF |
| $\mathrm{C}_{\text {PD }}$ |  |  | 40 |  |  |  |

7. Used to determine the no-load dynamic power consumption: $P_{D}=C_{P D} V_{C C}^{2 f}+I_{C C} V_{C C}$.

ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :--- | :---: | :---: |
| MC74HC245ADWG | SOIC-20 WIDE <br> (Pb-Free) | 38 Units / Rail |
| NLV74HC245ADWG* | SOIC-20 WIDE <br> (Pb-Free) | 38 Units / Rail |
| MC74HC245ADWR2G | SOIC-20 WIDE <br> (Pb-Free) | 1000 Tape \& Reel |
| NLV74HC245ADWR2G* | SOIC-20 WIDE <br> (Pb-Free) | 1000 Tape \& Reel |
| MC74HC245ADTG | TSSOP-20 <br> (Pb-Free) | 75 Units / Rail |
| NLV74HC245ADTG* | TSSOP-20 <br> (Pb-Free) | 75 Units / Rail |
| MC74HC245ADTR2G | TSSOP-20 <br> (Pb-Free) | 2500 Tape \& Reel |
| NLV74HC245ADTR2G* | TSSOP-20 <br> (Pb-Free) | 2500 Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.


Figure 1. Switching Waveform
*Includes all probe and jig capacitance
Figure 3. Test Circuit



Figure 2. Switching Waveform

EST POINT

| $\substack{\text { DEVICE } \\ \text { UNDER } \\ \text { TEST } \\ \\ \\ \text { OUTPUT }}$ |
| :---: | :---: |

Figure 4. Test Circuit

## MC74HC245A



Figure 5. Expanded Logic Diagram


SCALE 1:1


NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES

PER ASME Y14.5M, 1994
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION PROTRUSION. ALLOWABLE PROTRUSION
SHALL BE 0.13 TOTAL IN EXCESS OF B SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

| DIM | MILLIMETERS |  |
| :---: | ---: | ---: |
|  | MIN | MAX |
| A | 2.35 | 2.65 |
| A1 | 0.10 | 0.25 |
| b | 0.35 | 0.49 |
| $\mathbf{c}$ | 0.23 | 0.32 |
| D | 12.65 | 12.95 |
| E | 7.40 | 7.60 |
| e | 1.27 BSC |  |
| H | 10.05 | 10.55 |
| $\mathbf{h}$ | 0.25 | 0.75 |
| L | 0.50 | 0.90 |
| $\boldsymbol{\theta}$ | $0^{\circ}$ | $7^{\circ}$ |

GENERIC
MARKING DIAGRAM*


| XXXXX | $=$ Specific Device Code |
| :--- | :--- |
| A | $=$ Assembly Location |
| WL | $=$ Wafer Lot |
| YY | $=$ Year |
| WW | $=$ Work Week |
| G | $=$ Pb-Free Package |

*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-$ Free indicator, " G " or microdot " $\mathrm{\nabla}$ ", may or may not be present.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | SOIC-20 WB | PAGE 1 OF 1 |

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TSSOP-20 WB
CASE 948E
ISSUE D
DATE 17 FEB 2016

SCALE 2:1


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
CONTROLLING DIMENSION: MILLIMETER
2. DIMENSION A DOES NOT INCLUDE MOLD

FLASH, PROTRUSIONS OR GATE BURRS.
FLASH, PROTRUSIONS OR GATE BURRS.
MOLD FLASH OR GATE BURRS SHALL NO
EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE

INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED $0.25(0.010)$ PER SIDE
5. DIMENSION K DOES NOT INCLUDE

DAMBAR PROTRUSION. ALLOWABLE
DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

|  | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | MAX | MIN | MAX |
| A | 6.40 | 6.60 | 0.252 | 0.260 |
| B | 4.30 | 4.50 | 0.169 | 0.177 |
| C | --- | 1.20 | --- | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 BSC |  | 0.026 BSC |  |
| H | 0.27 | 0.37 | 0.011 | 0.015 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | BSC | 0.252 BSC |  |
| M | 0 | $0^{\circ}$ | $8^{\circ}$ | 0 |

GENERIC MARKING DIAGRAM* НРННННННН

|  | XXXX |
| :---: | :---: |
|  | XXXX |
|  | ALYW. |
| $\bigcirc$ | - |

A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

- = Pb-Free Package
(Note: Microdot may be in either location)
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-$ Free indicator, " G " or microdot " $\mathrm{\nabla}$ ", may or may not be present.
DIMENSIONS: MILLIMETERS

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | TSSOP-20 WB | PAGE 1 OF 1 |

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74LCXR162245MTX 74LVXC3245MTCX 74VHC245M 74VHC245MX JM38510/65553BRA FXL2TD245L10X 74LVC1T45GM,115
74LVC245ADTR2G TC74AC245P(F) SNJ54LS245FK 74LVT245BBT20-13 74AHC245D.112 74AHCT245D. 112
SN74LVCH16952ADGGR CY74FCT16245TPVCT 74AHCT245PW. 118 74LV245DB. 118 74LV245D. 112 74LV245PW. 112
74LVC2245APW. 112 74LVCH245AD. 112 SN75138NSR AP54RHC506ELT-R AP54RHC506BLT-R 74LVCR162245ZQLR
SN74LVCR16245AZQLR MC100EP16MNR4G MC100LVEP16MNR4G 714100R 74HCT643N MC100EP16DTR2G 5962-9221403MRA
74ALVC164245PAG 74FCT16245ATPAG 74FCT16245ATPVG 74FCT16245ETPAG 74FCT245CTSOG


[^0]:    Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond

